CentralSemiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

TIP100 TIP101 TIP102 NPN TIP105 TIP106 TIP107 PNP

SILICON POWER DARLINGTON COMPLEMENTARY TRANSISTORS

JEDEC TO-220AB CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR TIP100, TIP105 Series are Complementary Silicon Power Darlington Transistors designed for low speed switching and power amplifier applications

MAXIMUM	RATINGS	(T _C =25 ^O C)

	SYMBOL	TIP100 TIP105	TIP101 TIP106	TIP102 TIP107	UNIT
Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Current Collector Current (Peak) Base Current Power Dissipation Operating and Storage	VCBO VCEO VEBO IC ICM IB PD	60 60 5.0 8.0 15 1.0	80 80 5.0 8.0 15 1.0	100 100 5.0 8.0 15 1.0	V V A A A W
Junction Temperature	T _J , T _{stg}		-65 TO +150)	°c
Thermal Resistance	θJC	1.56	1.56	1.56	°c/w

ELECTRICAL CHARACTERISTICS (TC=25°C)

		TIP100		TIP101		TIP102		
SYMBOL	TEST CONDITIONS	MIN	105 MAX	TIP1	06 MAX	TIP1	07 MAX	UNIT
CBO CEO BVCEO VCE(SAT) VCE(SAT) VBE(ON) hFE hFE fT	V _{CB} =Rated V _{CBO} V _{CE} =½ Rated V _{CEO} V _{BE} =5.0V I _C =30mA I _C =3.0A, I _B =6.0mA I _C =8.0A, I _B =80mA V _{CE} =4.0V, I _C =8.0mA V _{CE} =4.0V, I _C =3.0A V _{CE} =4.0V, I _C =3.0A V _{CE} =4.0V, I _C =3.0A	60 1,000 200 4.0	50 50 8.0 2.0 2.5 2.8 20,000	80 1,000 200 4.0 MIN		200 4.0	1	μΑ μΑ mA V V V V
c_{ob}	V _{CB} =10V, I _E =0, f=0.1MHz (TIP100,	TIP101	١,	2.7.7	_	MAX		
c _{ob}	TIP102 ONLY) V _{CB} =10V, I _E =0, f=0.1MHz (TIP105,	T1P106	<u>.</u>			200		рF
	TIP107 ONLY)		•			300)	pF

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Datasheets for electronics components.